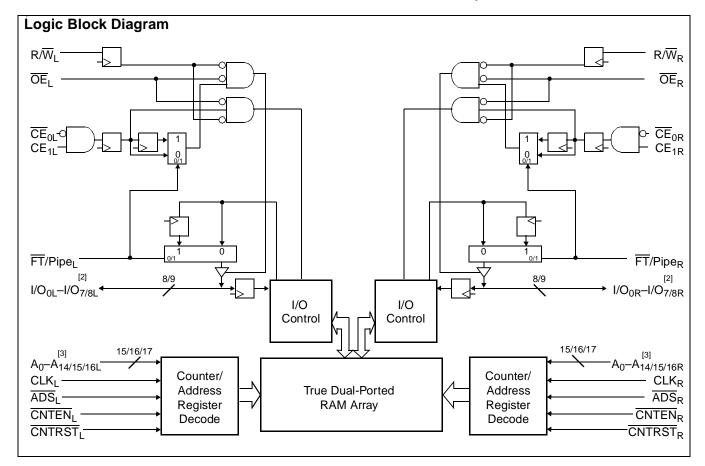


3.3V 32K/64K/128K x 8/9 Synchronous Dual-Port Static RAM

Features

- · True Dual-Ported memory cells which allow simultaneous access of the same memory location
- 6 Flow-Through/Pipelined devices
 - 32K x 8/9 organizations (CY7C09079V/179V)
 - 64K x 8/9 organizations (CY7C09089V/189V)
 - 128K x 8/9 organizations (CY7C09099V/199V)
- 3 Modes
 - Flow-Through
 - Pipelined
 - Burst
- · Pipelined output mode on both ports allows fast 83-MHz operation

- 0.35-micron CMOS for optimum speed/power
- High-speed clock to data access 7.5^[1]/9/12 ns (max.)
- 3.3V Low operating power
 - Active= 115 mA (typical)
 - Standby= 10 μA (typical)
- · Fully synchronous interface for easier operation
- · Burst counters increment addresses internally
 - Shorten cycle times
 - Minimize bus noise
 - Supported in Flow-Through and Pipelined modes
- · Dual Chip Enables for easy depth expansion
- Automatic power-down
- Commercial and Industrial temperature ranges
- Available in 100-pin TQFP



Notes:

- Call for availability. I/O $_0$ -I/O $_7$ for x8 devices; I/O $_0$ -I/O $_8$ for x9 devices.
- A₀-A₁₄ for 32K; A₀-A₁₅ for 64K; and A₀-A₁₆ for 128K devices.

For the most recent information, visit the Cypress web site at www.cypress.com



Functional Description

The CY7C09079V/89V/99V and CY7C09179V/89V/99V are high speed synchronous CMOS 32K, 64K, and 128K x 8/9 dual-port static RAMs. Two ports are provided, permitting independent, simultaneous access for reads and writes to any location in memory. [4] Registers on control, address, and data lines allow for minimal set-up and hold times. In pipelined output mode, data is registered for decreased cycle time. Clock to data valid $t_{CD2} = 7.5$ ns (pipelined). Flow-through mode can also be used to bypass the pipelined output register to eliminate access latency. In flow-through mode data will be available t_{CD1} = 18 ns after the address is clocked into the device. Pipelined output or flow-through mode is selected via the FT/Pipe pin.

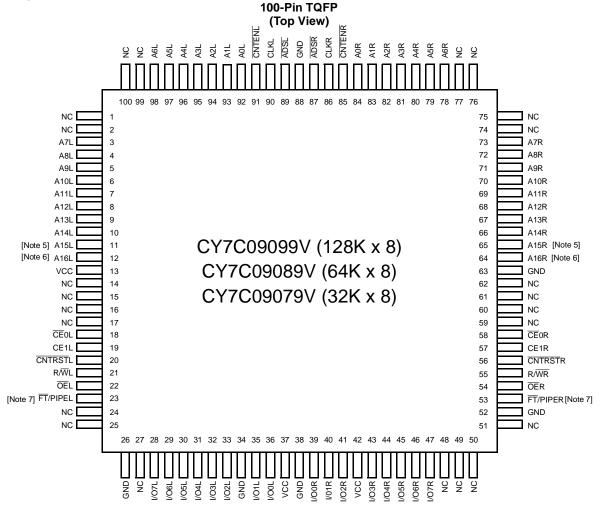
Each port contains a burst counter on the input address register. The internal write pulse width is independent of the LOW-to-HIGH transition of the clock signal. The internal write pulse is self-timed to allow the shortest possible cycle times.

A HIGH on CE₀ or LOW on CE₁ for one clock cycle will power down the internal circuitry to reduce the static power consumption. The use of multiple Chip Enables allows easier banking of multiple chips for depth expansion configurations. In the pipelined mode, one cycle is required with $\overline{\text{CE}}_0$ LOW and CE_1 HIGH to reactivate the outputs.

Counter enable inputs are provided to stall the operation of the address input and utilize the internal address generated by the internal counter for fast interleaved memory applications. A port's burst counter is loaded with the port's address strobe (ADS). When the port's count enable (CNTEN) is asserted, the address counter will increment on each LOW-to-HIGH transition of that port's clock signal. This will read/write one word from/into each successive address location until CNTEN is deasserted. The counter can address the entire memory array and will loop back to the start. Counter reset (CNTRST) is used to reset the burst counter.

All parts are available in 100-pin Thin Quad Plastic Flatpack (TQFP) packages.

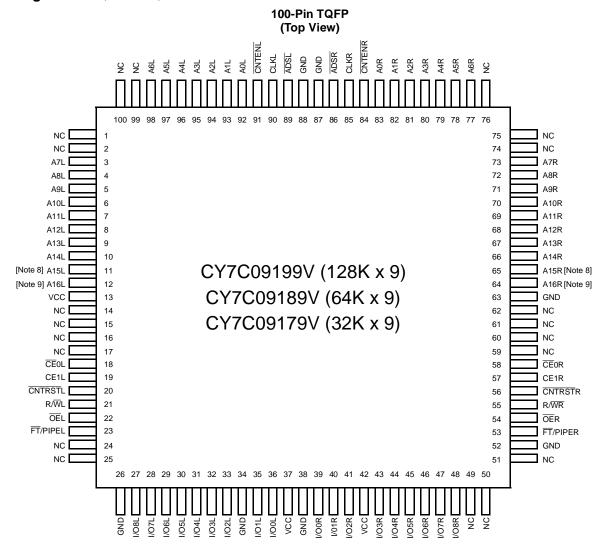
Pin Configurations



- When writing simultaneously to the same location, the final value cannot be guaranteed.
- This pin is NC for CY7C09079V.
 This pin is NC for CY7C09079V and CY7C09089V.
- For CY7C09079V and CY7C09089V, pin #23 connected to V_{CC} is pin compatible with an IDT 5V x8 pipelined device; connecting pin #23 and #53 to GND is pin compatible with an IDT 5V x16 flow-through device.



Pin Configurations (continued)



Selection Guide

	CY7C09079V/89V/99V CY7C09179V/89V/99V -7 ^[1]	CY7C09079V/89V/99V CY7C09179V/89V/99V -9	CY7C09079V/89V/99V CY7C09179V/89V/99V -12
f _{MAX2} (MHz) (Pipelined)	83	67	50
Max Access Time (ns) (Clock to data, Pipelined)	7.5	9	12
Typical Operating Current I _{CC} (mA)	155	135	115
Typical Standby Current for I _{SB1} (mA) (Both ports TTL Level)	25	20	20
Typical Standby Current for I _{SB3} (μA) (Both ports CMOS level)	10 μΑ	10 μΑ	10 μΑ

Shaded area contains advance information.

- This pin is NC for CY7C09179V.
 This pin is NC for CY7C09179V and CY7C09189V.



Pin Definitions

Left Port	Right Port	Description
A _{0L} -A _{16L}	A _{0R} -A _{16R}	Address Inputs (A ₀ –A ₁₄ for 32K; A ₀ –A ₁₅ for 64K; and A ₀ –A ₁₆ for 128K devices).
ADS _L	ADS _R	Address Strobe Input. Used as an address qualifier. This signal should be asserted LOW to access the part using an externally supplied address. Asserting this signal LOW also loads the burst counter with the address present on the address pins.
CE _{0L} ,CE _{1L}	CE _{0R} ,CE _{1R}	Chip Enable Input. To select either the left or right port, both \overline{CE}_0 AND CE_1 must be asserted to their active states ($\overline{CE}_0 \le V_{IL}$ and $CE_1 \ge V_{IH}$).
CLK _L	CLK _R	Clock Signal. This input can be free running or strobed. Maximum clock input rate is f _{MAX} .
CNTENL	CNTEN _R	Counter Enable Input. Asserting this signal <u>LOW</u> increments the <u>burst</u> address counter of its respective port on each rising edge of CLK. <u>CNTEN</u> is disabled if <u>ADS</u> or <u>CNTRST</u> are asserted LOW.
CNTRST _L	CNTRST _R	Counter Reset Input. Asserting this signal LOW resets the burst address counter of its respective port to zero. CNTRST is not disabled by asserting ADS or CNTEN.
I/O _{0L} -I/O _{8L}	I/O _{0R} –I/O _{8R}	Data Bus Input/Output (I/O ₀ –I/O ₇ for x8 devices; I/O ₀ –I/O ₈ for x9 devices).
ŌE _L	ŌE _R	Output Enable Input. This signal must be asserted LOW to enable the I/O data pins during read operations.
R/W _L	R/W _R	Read/Write Enable Input. This signal is asserted LOW to write to the dual port memory array. For read operations, assert this pin HIGH.
FT/PIPE _L	FT/PIPE _R	Flow-Through/Pipelined Select Input. For flow-through mode operation, assert this pin LOW. For pipelined mode operation, assert this pin HIGH.
GND	•	Ground Input.
NC		No Connect.
V _{CC}		Power Input.

Maximum Ratings

Static Discharge Voltage	>1100V
Latch-Up Current	>200mA

Operating Range

Range	Ambient Temperature	v _{cc}
Commercial	0°C to +70°C	3.3V ± 300 mV
Industrial	-40°C to +85°C	3.3V ± 300 mV

Shaded area contains advance information.



Electrical Characteristics Over the Operating Range

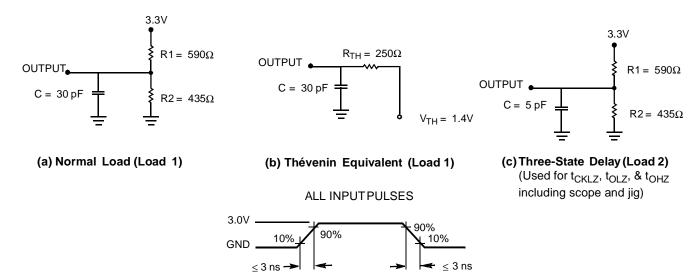
			CY7C09079V/89V/99V CY7C09179V/89V/99V									
				-7 ^[1]			-9			-12		
Symbol	Parameter		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Units
V _{OH}	Output HIGH Voltage (V _{CC} =Min, I _{OH} =	–4.0mA)	2.4			2.4			2.4			V
V _{OL}	Output LOW Voltage (V _{CC} =Min, I _{OH} =	+4.0mA)			0.4			0.4			0.4	V
V _{IH}	Input HIGH Voltage	2.2			2.2			2.2			V	
V _{IL}	Input LOW Voltage			0.8			0.8			0.8	V	
I _{OZ}	Output Leakage Current	-10		10	-10		10	-10		10	μΑ	
I _{CC}	Operating Current (V _{CC} =Max,	Com'l.		155	275		135	230		115	180	mΑ
	I _{OUT} =0 mA) Outputs Disabled	Indust.					185	300		155	250	mA
I _{SB1}	Standby Current (Both Ports TTL Level) $CE_L \& CE_R \ge V_{IH}$, $f = f_{MAX}$	Com'l.		25	85		20	75		20	70	mA
	Level) ^[10] CE _L & CE _R ≥ V _{IH} , f=f _{MAX}	Indust.					35	85		30	80	mA
I _{SB2}	Standby Current (One Port TTL Level) ^[10] $\overline{CE}_L \mid \overline{CE}_R \ge V_{IH}$, f=f _{MAX}	Com'l.		105	165		95	155		85	140	mA
	Level) ^[10] CE _L CE _R ≥ V _{IH} , f=f _{MAX}	Indust.					105	165		95	150	mA
I _{SB3}	Standby Current (Both Ports CMOS Level) $\overline{CE}_L \& \overline{CE}_R \ge V_{CC} - 0.2V$,	Com'l.		10	100		10	100		10	100	μΑ
	$f=0$ Level) ^{L(o)} CE _L & CE _R \geq V _{CC} $-$ 0.2V,	Indust.					10	100		10	100	μА
I _{SB4}	Standby Current (One Port CMOS	Com'l.		95	125		85	115		75	100	mA
	Level) $[10]$ $\overline{CE}_L \mid \overline{CE}_R \ge V_{IH}$, $f = f_{MAX}$	Indust.					95	125		85	110	mA

Shaded area contains advance information.

Capacitance

Parameter	Parameter Description		Max.	Unit	
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	10	pF	
C _{OUT}	Output Capacitance	$V_{CC} = 3.3V$	10	pF	

AC Test Loads



Note:

10. \overline{CE}_L and \overline{CE}_R are internal signals. To select either the left or right port, both \overline{CE}_0 AND CE_1 must be asserted to their active states ($\overline{CE}_0 \le V_{IL}$ and $CE_1 \ge V_{IH}$).



Switching Characteristics Over the Operating Range

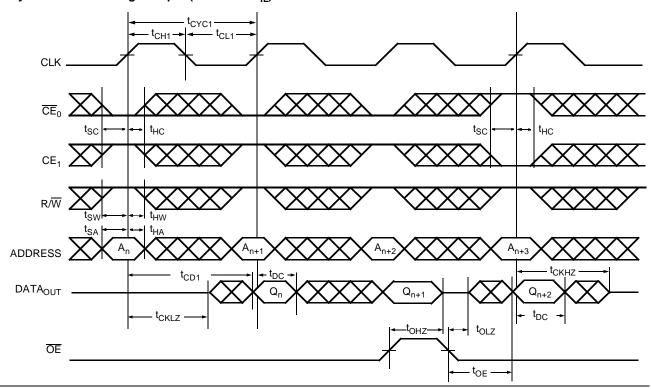
			CY7C09079V/89V/99V CY7C09179V/89V/99V						
		-7	, [1]	-	9	-1	12		
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Units	
f _{MAX1}	f _{Max} Flow-Through		45		40		33	MHz	
f _{MAX2}	f _{Max} Pipelined		83		67		50	MHz	
t _{CYC1}	Clock Cycle Time - Flow-Through	22		25		30		ns	
t _{CYC2}	Clock Cycle Time - Pipelined	12		15		20		ns	
t _{CH1}	Clock HIGH Time - Flow-Through	7.5		12		12		ns	
t _{CL1}	Clock LOW Time - Flow-Through	7.5		12		12		ns	
t _{CH2}	Clock HIGH Time - Pipelined	5		6		8		ns	
t _{CL2}	Clock LOW Time - Pipelined	5		6		8		ns	
t _R	Clock Rise Time		3		3		3	ns	
t _F	Clock Fall Time		3		3		3	ns	
t _{SA}	Address Set-Up Time	4		4		4		ns	
t _{HA}	Address Hold Time	0		1		1		ns	
t _{SC}	Chip Enable Set-Up Time	4		4		4		ns	
t _{HC}	Chip Enable Hold Time	0		1		1		ns	
t _{SW}	R/W Set-Up Time	4		4		4		ns	
t _{HW}	R/W Hold Time	0		1		1		ns	
t _{SD}	Input Data Set-Up Time	4		4		4		ns	
t _{HD}	Input Data Hold Time	0		1		1		ns	
t _{SAD}	ADS Set-Up Time	4		4		4		ns	
t _{HAD}	ADS Hold Time	0		1		1		ns	
t _{SCN}	CNTEN Set-Up Time	4.5		5		5		ns	
t _{HCN}	CNTEN Hold Time	0		1		1		ns	
t _{SRST}	CNTRST Set-Up Time	4		4		4		ns	
t _{HRST}	CNTRST Hold Time	0		1		1		ns	
toF	Output Enable to Data Valid		9		10		12	ns	
t _{OLZ} [11,12]	OE to Low Z	2		2		2		ns	
t _{OHZ} [11,12]	OE to High Z	1	7	1	7	1	7	ns	
t _{CD1}	Clock to Data Valid - Flow-Through		18		20		25	ns	
t _{CD2}	Clock to Data Valid - Pipelined		7.5		9		12	ns	
tnc	Data Output Hold After Clock HIGH	2		2		2		ns	
t _{CKHZ} [11,12]	Clock HIGH to Output High Z	2	9	2	9	2	9	ns	
t _{CKLZ} [11,12]	Clock HIGH to Output Low Z	2		2		2		ns	
Port to Port	t Delays								
t _{CWDD}	Write Port Clock HIGH to Read Data Delay		35		40		40	ns	
t _{CCS}	Clock to Clock Set-Up Time		10		15		15	ns	

^{11.} Test conditions used are Load 2.12. This parameter is guaranteed by design, but it is not production tested.

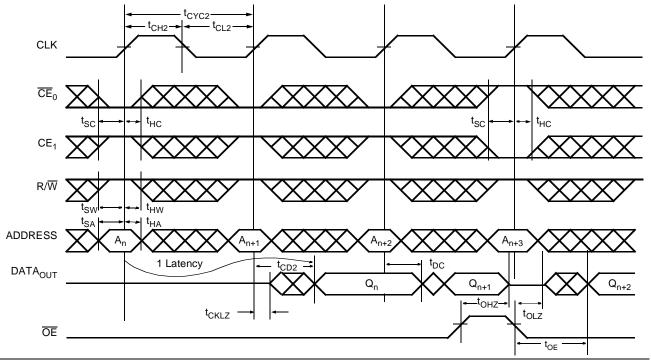


Switching Waveforms

Read Cycle for Flow-Through Output $(\overline{FT}/PIPE = V_{IL})^{[13,14,15,16]}$



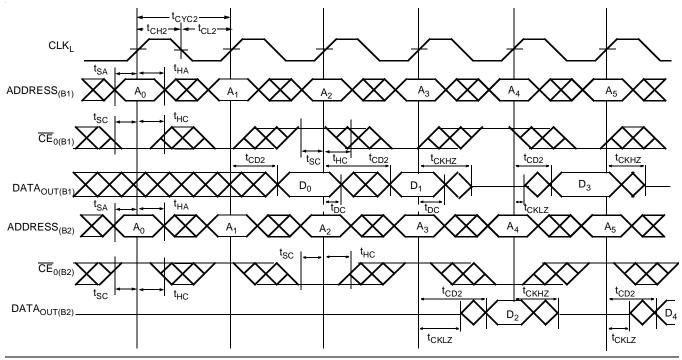
Read Cycle for Pipelined Operation $\overline{(FT/PIPE = V_{IH})^{[13,14,15,16]}}$



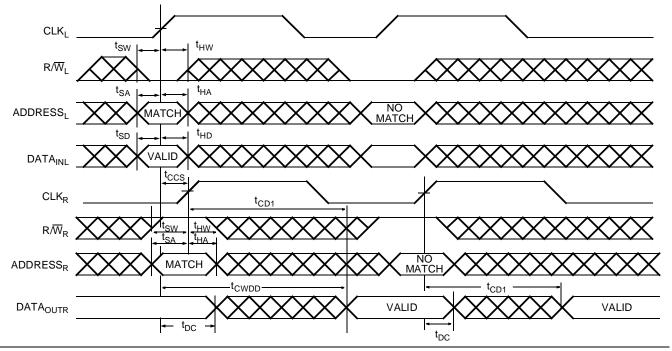
- 13. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
 14. ADS = V_{IL}, CNTEN and CNTRST = V_{IH}
 15. The output is disabled (high-impedance state) by CE₀=V_{IH} or CE₁ = V_{IL} following the next rising edge of the clock.
 16. Addresses do not have to be accessed sequentially since ADS = V_{IL} constantly loads the address on the rising edge of the CLK. Numbers are for reference only.



Bank Select Pipelined Read^[17,18]



Left Port Write to Flow-Through Right Port Read^[19,20,21,22]

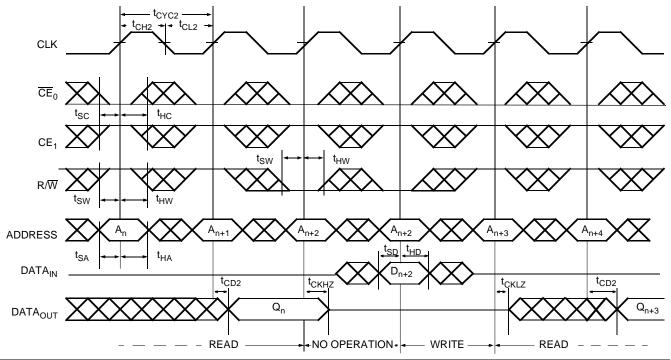


- 17. In this depth expansion example, B1 represents Bank #1 and B2 is Bank #2; Each Bank consists of one Cypress dual-port device from this datasheet.

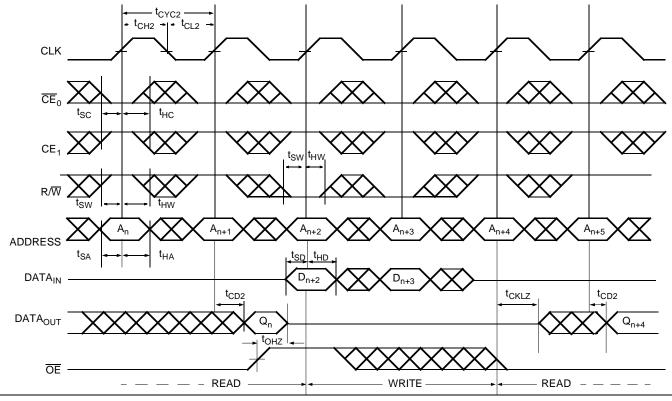
- In this depth expansion example, B1 represents Bank #1 and B2 is Bank #2; Each Bank consists of one Cypress dual-port device from this datasheet. ADDRESS_(B1) = ADDRESS_(B2). OE and $\overline{ADS} = V_{IL}$, $\overline{CE}_{1(B1)}$, $\overline{CE}_{1(B2)}$, $\overline{CE}_{$



Pipelined Read-to-Write-to-Read ($\overline{\rm OE}$ = V_{IL})^[16,23,24,25]



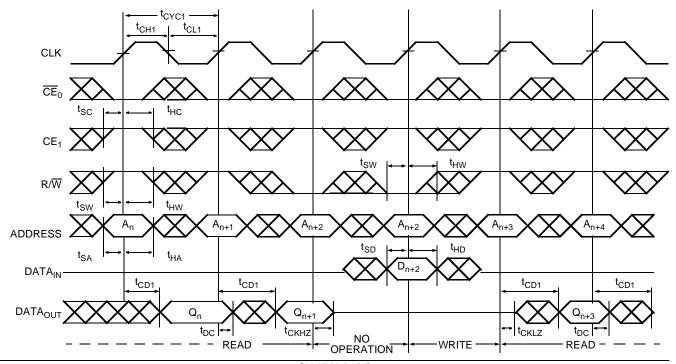
Pipelined Read-to-Write-to-Read (OE Controlled)[16,23,24,25]



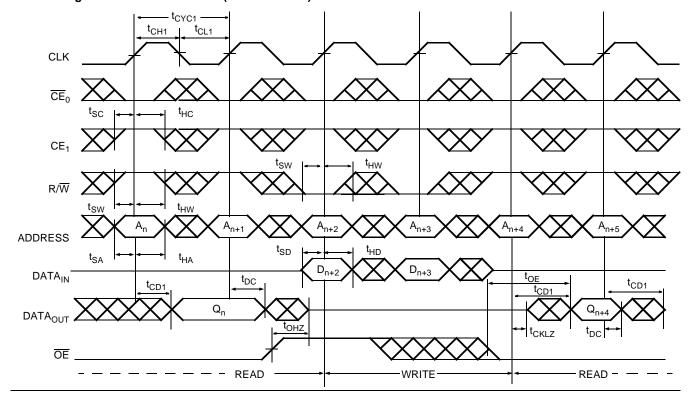
- 23. Output state (HIGH, LOW, or High-Impedance) is determined by the previous cycle control signals.
 24. CE₀ and ADS = V_{IL}; CE₁, CNTEN, and CNTRST = V_{IH}.
 25. During "No operation", data in memory at the selected address may be corrupted and should be re-written to ensure data integrity.



Flow-Through Read-to-Write-to-Read ($\overline{\text{OE}} = \text{V}_{\text{IL}}$)[14,16,23,24,25]

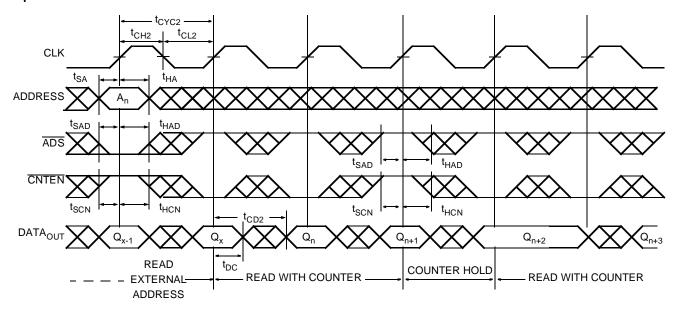


Flow-Through Read-to-Write-to-Read (OE Controlled)[14,17,23,24,25]

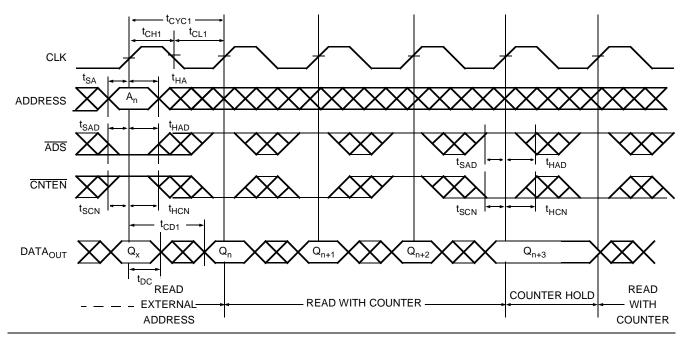




Pipelined Read with Address Counter Advance^[26]



Flow-Through Read with Address Counter Advance [26]

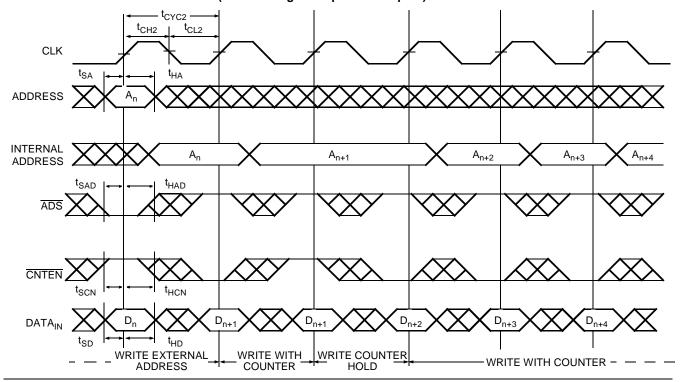


Note:

26. \overline{CE}_0 and $\overline{OE} = V_{IL}$; CE_1 , R/\overline{W} and $\overline{CNTRST} = V_{IH}$.



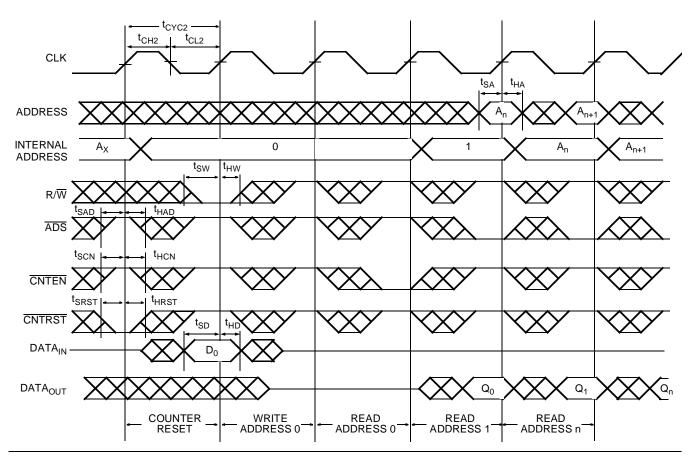
Write with Address Counter Advance (Flow-Through or Pipelined Outputs)^[27,28]



- 27. \overline{CE}_0 \text{ and } R\overline{W} = V_{IL}; CE_1 \text{ and } \overline{CNTRST} = V_{IH}.
 28. The "Internal Address" is equal to the "External Address" when \overline{ADS} = V_{IL} \text{ and equals the counter output when } \overline{ADS} = V_{IH}.



Counter Reset (Pipelined Outputs)^[16,23,29,30]



Notes:

29. \$\overline{CE}_0 = V_{|L|}\$; \$CE_1 = V_{|H|}\$.
 30. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset.



Read/Write and Enable Operation^[31,32,33]

		Inputs		Outputs		
OE	CLK	CE ₀	CE ₁	R/W	I/O ₀ –I/O ₉	Operation
Х		Н	Х	Х	High-Z	Deselected ^[34]
Х		Х	L	Х	High-Z	Deselected ^[34]
Х	4	Ш	Ι	L	D _{IN}	Write
L		L	Ι	Н	D _{OUT}	Read ^[34]
Н	Х	L	Н	Х	High-Z	Outputs Disabled

Address Counter Control Operation[31,35,36,37]

Address	Previous Address	CLK	ADS	CNTEN	CNTRST	I/O	Mode	Operation
Х	Х	7	Х	Х	L	D _{out(0)}	Reset	Counter Reset to Address 0
A _n	Х		L	Х	Н	D _{out(n)}	Load	Address Load into Counter
Х	A _n	7	Н	Н	Н	D _{out(n)}	Hold	External Address Blocked—Counter Disabled
Х	A _n	7	Н	L	Н	D _{out(n+1)}	Increment	Counter Enabled—Internal Address Generation

- Notes:

 31. "X" = Don't Care, "H" = V_{IH}, "L" = V_{IL}.

 32. ADS, CNTEN, CNTRST = Don't Care.

 33. OE is an asynchronous input signal.

 34. When CE changes state in the pipelined mode, deselection and read happen in the following clock cycle.

 35. CE₀ and OE = V_{IL}; CE₁ and R/W = V_{IH}.

 36. Data shown for flow-through mode; pipelined mode output will be delayed by one cycle.

 37. Counter operation is independent of CE₀ and CE₁.



Ordering Information

32K x8 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
7.5 ^[1]	CY7C09079V-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
9	CY7C09079V-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09079V-9AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09079V-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09079V-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

Shaded area contains advance information.

64K x8 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
7.5 ^[1]	CY7C09089V-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
9	CY7C09089V-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09089V-9AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09089V-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09089V-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

Shaded area contains advance information.

128K x8 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
7.5 ^[1]	CY7C09099V-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
9	CY7C09099V-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09099V-9AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09099V-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09099V-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

Shaded area contains advance information.

32K x9 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
7.5 ^[1]	CY7C09179V-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
9	CY7C09179V-9C	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09179V-9AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09179V-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09179V-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

Shaded area contains advance information.

64K x9 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
7.5 ^[1]	CY7C09189V-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
9	CY7C09189V-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09189V-9AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09189V-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09189V-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

Shaded area contains advance information.



Ordering Information (continued)

128K x9 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
7.5 ^[1]	CY7C09199V-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
9	CY7C09199V-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09199V-9AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09199V-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09199V-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

Shaded area contains advance information.

Document #: 38-00667-D

Package Diagram

100-Pin Thin Plastic Quad Flat Pack (TQFP) A100

